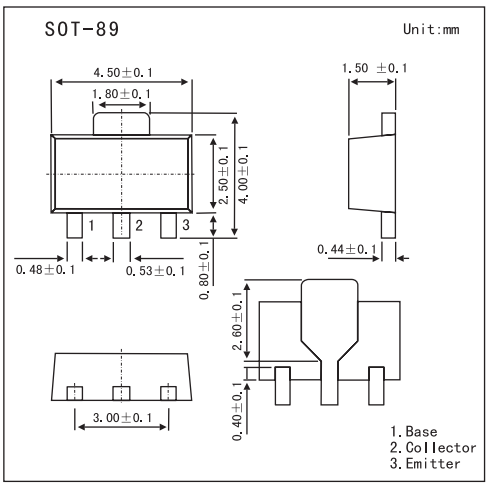
TY Semicondutor®

Product specification

2SA1368



■ Features

- High Voltage V_{CEO} = -100V
- High Collector Current (I_{CM} = -800mA)
- High Collector Dissipation P_C = 500mW
- Small Package For Mounting
- Complementary to 2SC3438

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Peak Collector Current	I_{CM}	-800	mA
Collector Power Dissipation	P_C	500	mW
Jumction temperature	T_j	150	℃
Storage temperature Range	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	V_{CB} = -50V , I_E = 0			-0.5	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = -2V , I_C = 0			-0.5	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = -1mA , R_{BE} = ∞	-100			V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = -10μA , I_E = 0	-100			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = -10μA , I_C = 0	-5			V
DC Current Gain	h_{FE}	V_{CE} = -10V , I_C = -10mA	55		300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -150mA , I_B = -15mA		-0.15	-0.5	V
Transition Frequency	f_T	V_{CE} = -10V , I_E = 10mA		130		MHz
Collector Output Capacitance	C_{ob}	V_{CB} = -10V , I_E = 0 , f = 1MHz		11		pF

■ h_{FE} Classification

Marking	E		
Rank	C	D	E
hFE	55 ～ 110	90 ～ 180	150 ～ 300

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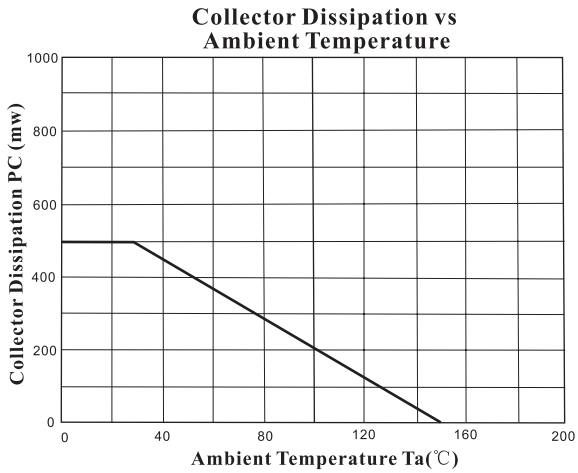
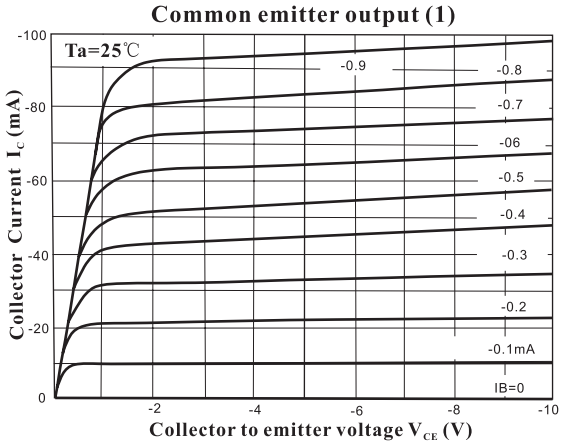
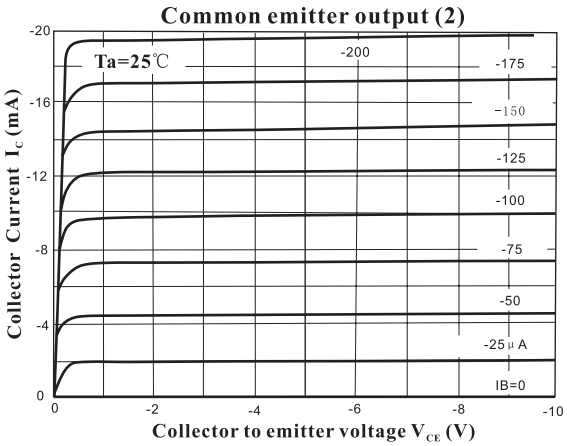
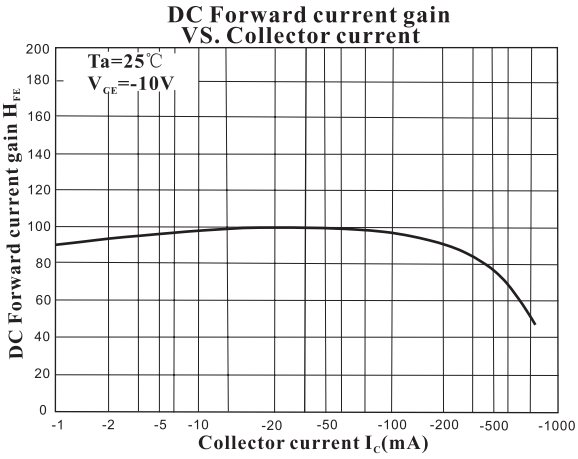
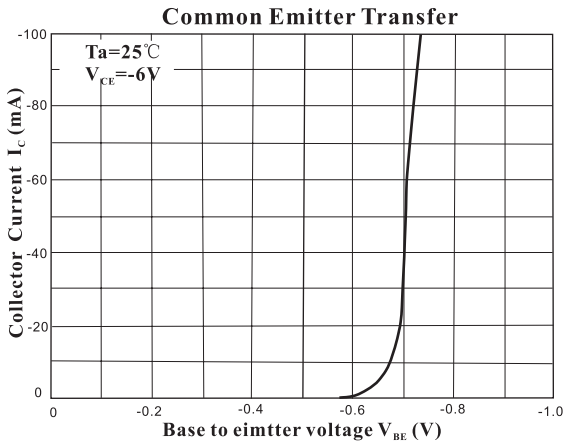
■ Electrical Characteristics Curves

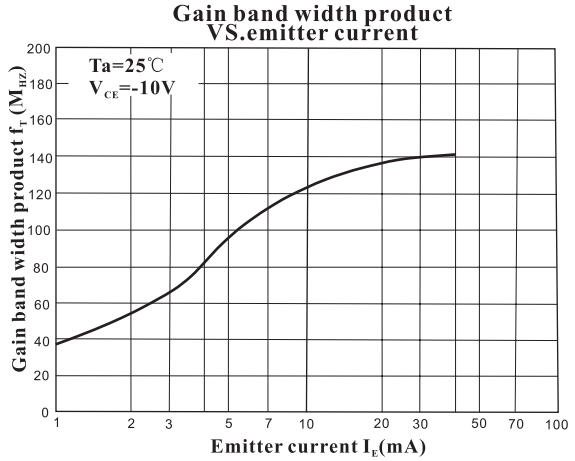












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